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Details	
Product Status	Discontinued at Digi-Key
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Program Memory Type	-
Controller Series	-
RAM Size	-
Interface	-
Number of I/O	-
Voltage - Supply	-
Operating Temperature	-
Mounting Type	-
Package / Case	M3.2 Chip Card Module
Supplier Device Package	M3.2 Chip Card Module
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SIEMENS

ICs for Chip Cards

Intelligent 256-Byte EEPROM
SLE 4432/SLE 4442

Data Sheet 07.95

SLE 4432/SLE4442 **Revision History:** **Original Version 07.95**	
Previous Releases: 01.94	
Page	Subjects (changes since last revision)
	Editorial changes

This edition was realized using the software system FrameMaker®

Important:	For further information please contact: Siemens Semiconductor Group in Munich, Germany, Key Account Service Chip Card ICs and Identsystem ICs, Tel.: + 49 89 4144-4362, Fax + 49 89 4144-2360 The supply of this component does not include a licence for its use in smart card applications. This licence is due to: INNOVATRON Patents 137 Boulevard de Sébastopol, 75002 Paris, France, Fax + 33 1 40 13 39 09

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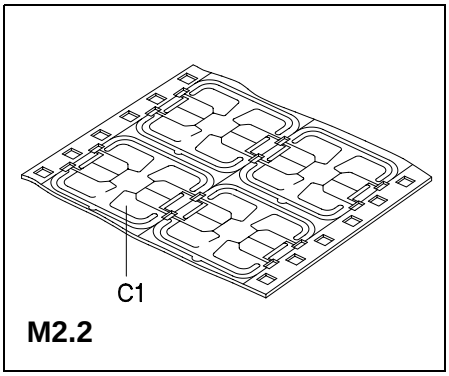
SIEMENS

Intelligent 256-Byte EEPROM with Write Protect Function SLE 4432

Intelligent 256-Byte EEPROM with Write Protect Function and Programmable Security Code (PSC) SLE 4442

Features

- 256 × 8-bit EEPROM organization
- Byte-wise addressing
- Irreversible byte-wise write protection of lowest 32 addresses (Byte 0 ... 31)
- 32 × 1-bit organization of protection memory
- Two-wire link protocol
- End of processing indicated at data output
- Answer-to-Reset acc. to ISO standard 7816-3
- Programming time 2.5 ms per byte for both erasing and writing
- Minimum of 10^4 write/erase cycles[1)]
- Data retention for minimum of ten years[1)]
- Contact configuration and serial interface in accordance with ISO standard 7816 (synchronous transmission)



M2.2

Additional Feature of SLE 4442

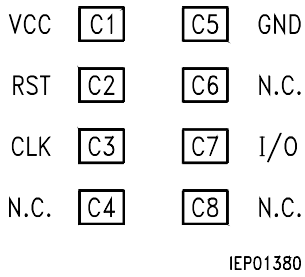
- Data can only be changed after entry of the correct 3-byte programmable security code (security memory)

Type	Ordering Code	Package
SLE 4432 M2.2	on request	Wire-Bonded Module M2.2
SLE 4432 C	on request	Chip
SLE 4442 M2.2	on request	Wire-Bonded Module M2.2
SLE 4442 C	on request	Chip

1) Values are temperature dependent, for further information please refer to your Siemens sales office.

1 Pin Configuration

(top view)



M2.2 (Card Contacts)

Pin Definitions and Functions

Card Contact	Symbol	Function
C1	VCC	Supply voltage
C2	RST	Reset
C3	CLK	Clock input
C4	N.C.	Not connected
C5	GND	Ground
C6	N.C.	Not connected
C7	I/O	Bidirectional data line (open drain)
C8	N.C.	Not connected

SLE 4432/SLE 4442 comes as a M2.2 wire-bonded module for embedding in plastic cards or as a die for customer packaging.

Table 1

Byte 1 Control								Byte 2 Address	Byte 3 Data	Operation	Mode
B7	**B6**	**B5**	**B4**	**B3**	**B2**	**B1**	**B0**	**A7-A0**	**D7-D0**		
0	0	1	1	0	0	0	0	address	no effect	READ MAIN MEMORY	outgoing data
0	0	1	1	1	0	0	0	address	input data	UPDATE MAIN MEMORY	processing
0	0	1	1	0	1	0	0	no effect	no effect	READ PROTECTION MEMORY	outgoing data
0	0	1	1	1	1	0	0	address	input data	WRITE PROTECTION MEMORY	processing

Table 2
SLE 4442 only

0	0	1	1	0	0	0	1	no effect	no effect	READ SECURITY MEMORY	outgoing data
0	0	1	1	1	0	0	1	address	input data	UPDATE SECURITY MEMORY	processing
0	0	1	1	0	0	1	1	address	input data	COMPARE VERIFICATION DATA	processing

2.3.1 Read Main Memory (SLE 4432 and SLE 4442)

The command reads out the contents of the main memory (with LSB first) starting at the given byte address (N = 0…255) up to the end of the memory. After the command entry the IFD has to supply sufficient clock pulses. The number of clocks is m = (256 – N) × 8 + 1. The read access to the main memory is always possible.

Address (decimal)	Main Memory	Protection Memory	Security Memory (only SLE 4442)
255	Data Byte 255 (D7 … D0)	–	–
:	:	–	–
32	Data Byte 32 (D7 … D0)	–	–
31	Data Byte 31 (D7 … D0)	Protection Bit 31 (D31)	–
:	:	:	–
3	Data Byte 3 (D7 … D0)	Protection Bit 3 (D3)	Reference Data Byte 3 (D7 … D0)
2	Data Byte 2 (D7 … D0)	Protection Bit 2 (D2)	Reference Data Byte 2 (D7 … D0)
1	Data Byte 1 (D7 … D0)	Protection Bit 1 (D1)	Reference Data Byte 1 (D7 … D0)
0	Data Byte 0 (D7 … D0)	Protection Bit 0 (D0)	Error Counter

Command: READ MAIN MEMORY

	Control								Address	Data
	B7	B6	B5	B4	B3	B2	B1	B0	A7…A0	D7…D0
Binary	0	0	1	1	0	0	0	0	Address	No effect
Hexadecimal	30_H								00_H…FF_H	No effect

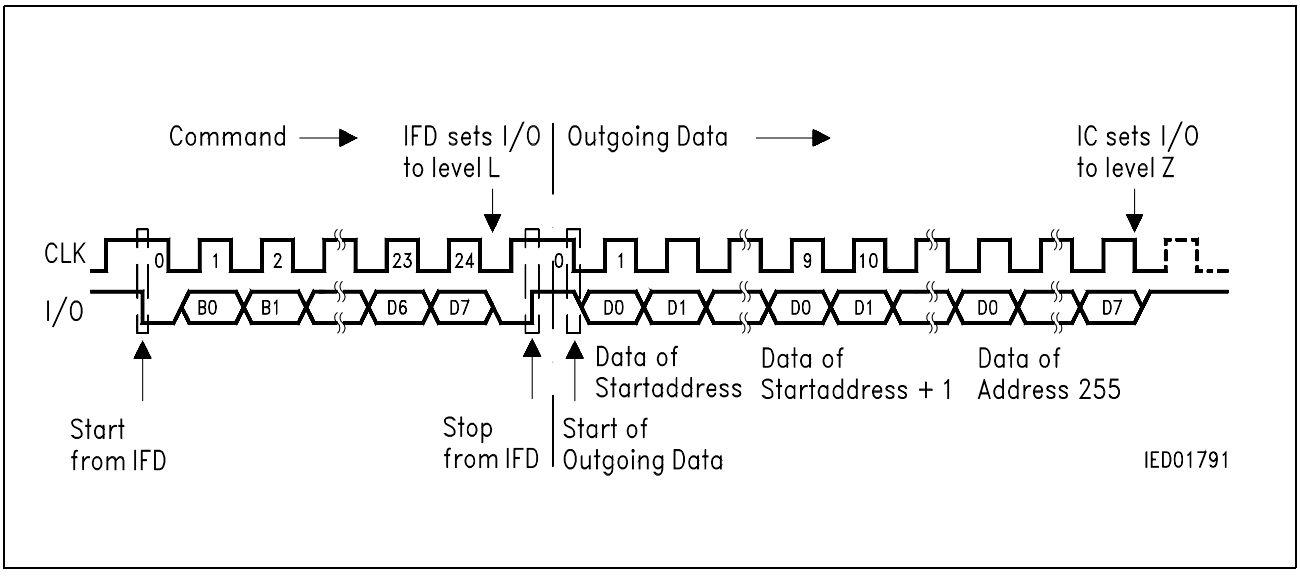


Figure 5
Read Main Memory

2.3.3 Update Main Memory (SLE 4432 and SLE 4442)

The command programs the addressed EEPROM byte with the data byte transmitted. Depending on the old and new data, one of the following sequences will take place during the processing mode:

- erase and write (5 ms) corresponding to m = 255 clock pulses
- write without erase (2.5 ms) corresponding to m = 124 clock pulses
- erase without write (2.5 ms) corresponding to m = 124 clock pulses

(All values at 50 kHz clock rate.)

Address (decimal)	Main Memory	Protection Memory	Security Memory (only SLE 4442)
255	Data Byte 255 (D7 … D0)	–	–
:	:	–	–
32	Data Byte 32 (D7 … D0)	–	–
31	Data Byte 31 (D7 … D0)	Protection Bit 31 (D31)	–
:	:	:	–
3	Data Byte 3 (D7 … D0)	Protection Bit 3 (D3)	Reference Data Byte 3 (D7 … D0)
2	Data Byte 2 (D7 … D0)	Protection Bit 2 (D2)	Reference Data Byte 2 (D7 … D0)
1	Data Byte 1 (D7 … D0)	Protection Bit 1 (D1)	Reference Data Byte 1 (D7 … D0)
0	Data Byte 0 (D7 … D0)	Protection Bit 0 (D0)	Error Counter

Command: UPDATE MAIN MEMORY

	Control								Address	Data
	B7	B6	B5	B4	B3	B2	B1	B0	A7…A0	D7…D0
Binary	0	0	1	1	1	0	0	0	Address	Input data
Hexadecimal	38_H								00_H…FF_H	Input data

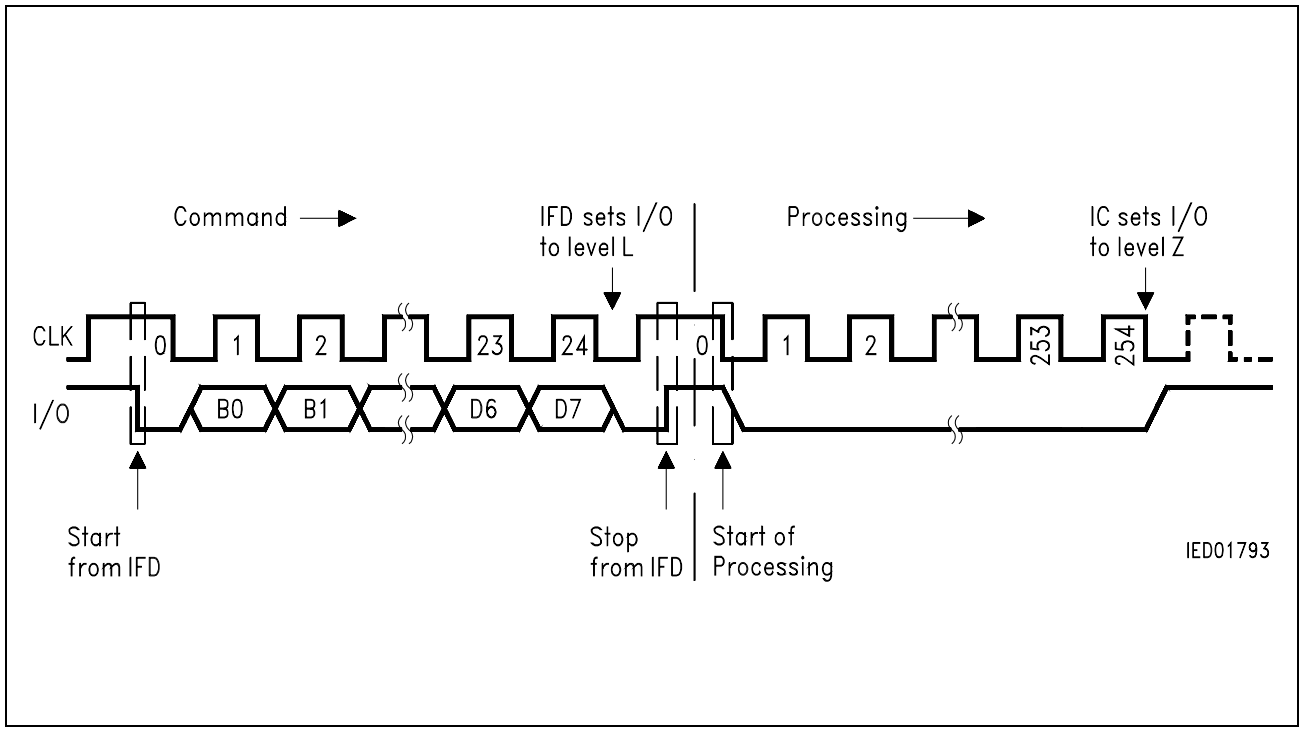


Figure 7
Erase and Write Main Memory

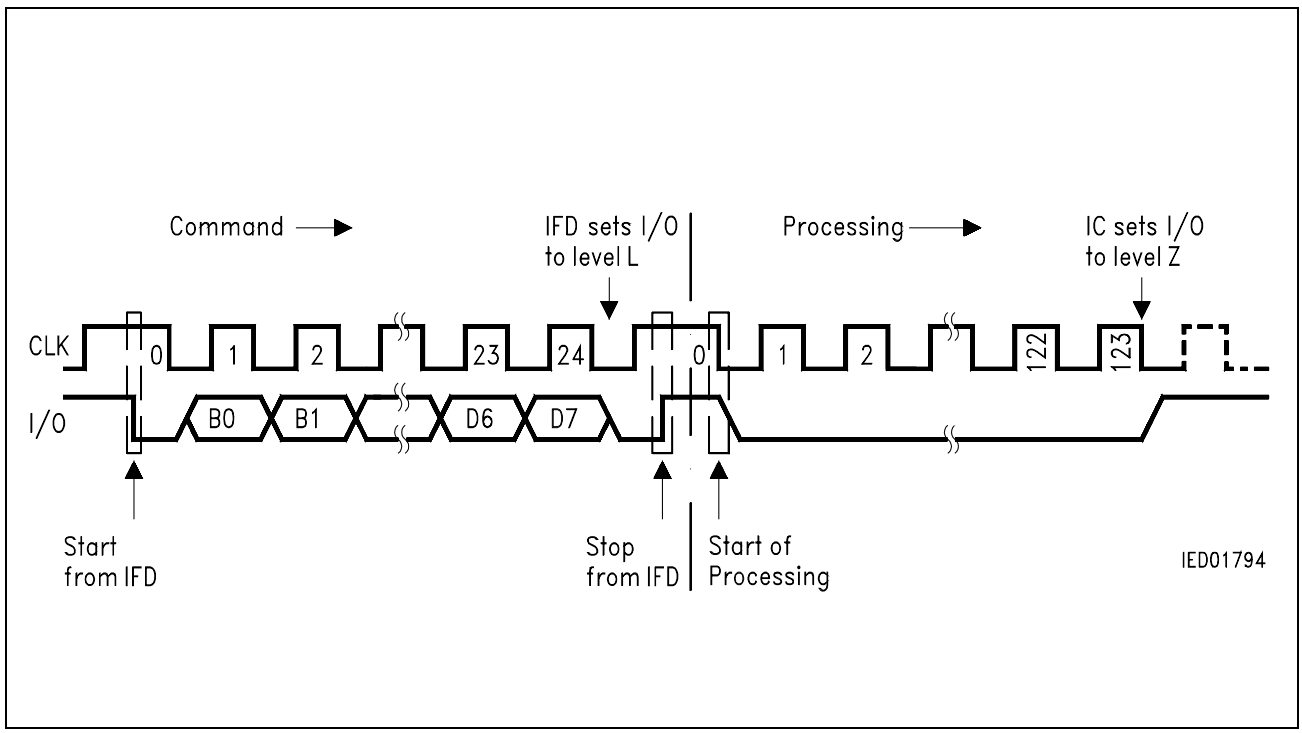


Figure 8
Erase or Write Main Memory

If the addressed byte is protected against changes (indicated by the associated written protection bit) the I/O is set to high impedance after the clock number 2 of the processing.

2.3.5 Read Security Memory (SLE 4442 only)

Similar to the read command for the protection memory this command reads out the 4 bytes of the security memory. The number of clock pulses during the outgoing data mode is 32. I/O is switched to high impedance Z by an additional pulse. Without a preceeding successful verification of the PSC the output of the reference bytes is suppressed, that means I/O outputs state L for the reference data bytes.

Address (decimal)	Main Memory	Protection Memory	Security Memory (only SLE 4442)
255	Data Byte 255 (D7 … D0)	–	–
:	:	–	–
32	Data Byte 32 (D7 … D0)	–	–
31	Data Byte 31 (D7 … D0)	Protection Bit 31 (D31)	–
:	:	:	–
3	Data Byte 3 (D7 … D0)	Protection Bit 3 (D3)	Reference Data Byte 3(D7 … D0)
2	Data Byte 2 (D7 … D0)	Protection Bit 2 (D2)	Reference Data Byte 2(D7 … D0)
1	Data Byte 1 (D7 … D0)	Protection Bit 1 (D1)	Reference Data Byte 1(D7 … D0)
0	Data Byte 0 (D7 … D0)	Protection Bit 0 (D0)	Error Counter (0,0,0,0,0,D2,D1,D0)

Command: READ SECURITY MEMORY

	Control								Address	Data
	B7	B6	B5	B4	B3	B2	B1	B0	A7…A0	D7…D0
Binary	0	0	1	1	0	0	0	1	No effect	No effect
Hexadecimal	31_H								No effect	No effect

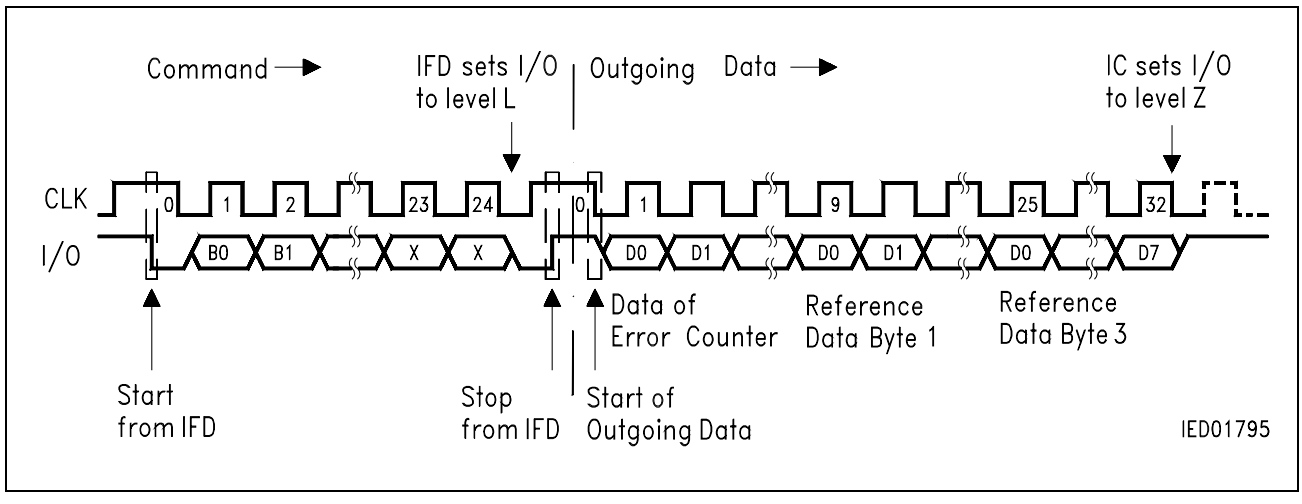


Figure 9
Read Security Memory

2.4 PSC Verification (SLE 4442 only)

The SLE 4442 requires a correct verification of the Programmable Security Code PSC stored in the Security Memory for altering data if desired.

The following procedure has to be carried out exactly as described. Any variation leads to a failure, so that a write/erase access will not be achieved. As long as the procedure has not been successfully concluded the error counter bits can only be changed from “1” to “0” but not erased.

At first an error counter bit has to be written to “0” by an UPDATE command (**see figure 11**) followed by three COMPARE VERIFICATION DATA commands beginning with byte 1 of the reference data. A successful conclusion of the whole procedure can be recognized by being able to erase the error counter which is not automatically erased. Now write/erase access to all memory areas is possible as long as the operating voltage is applied. In case of error the whole procedure can be repeated as long as erased counter bits are available. Having been enabled, the reference data are allowed to be altered like any other information in the EEPROM.

The following table gives an overview of the necessary commands for the PSC verification. The sequence of the shaded commands is mandatory.

Command	**Control**	**Address**	**Data**	**Remark**
	B7…B0	**A7…A0**	**D7…D0**	
Read security Memory	31_H	No effect	No effect	Check Error Counter
Update Security Memory	39_H	00_H	Input data	Write free bit in Error Counter input data: 0000 0ddd binary
Compare Verification Data	33_H	01_H	Input data	Reference Data Byte 1
Compare Verification Data	33_H	02_H	Input data	Reference Data Byte 2
Compare Verification Data	33_H	03_H	Input data	Reference Data Byte 3
Update Security Memory	39_H	00_H	FF_H	Erase Error Counter
Read Security Memory	31_H	No effect	No effect	Check Error Counter

As shipped, the PSC is programmed with a code according to individual agreement with the customer. Thus, knowledge of this code is indispensable to alter data.

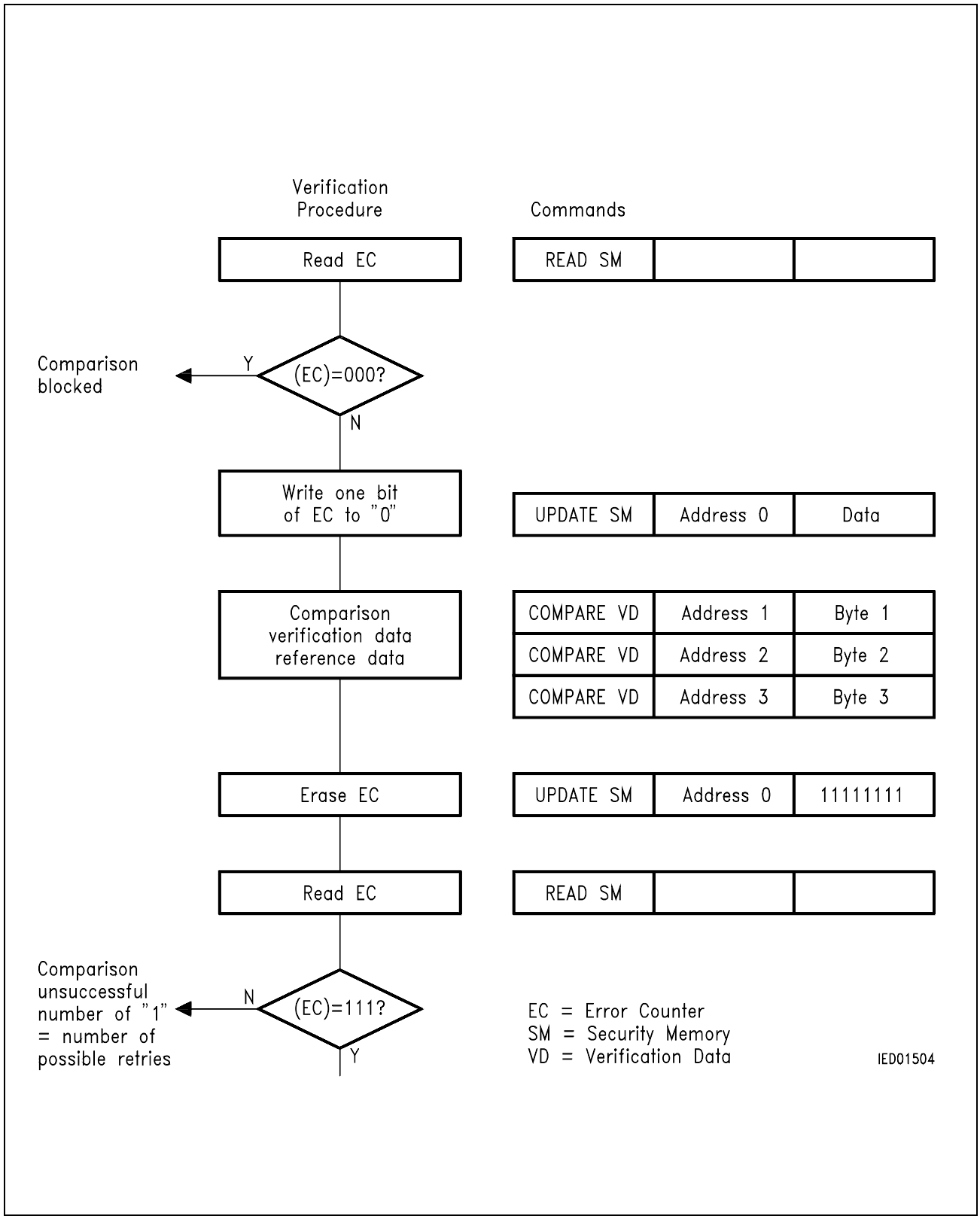


Figure 11
Verification Procedure

2.5 Reset Modes

Reset and Answer-to-Reset (compare 2.2.1)

Power on Reset

After connecting the operating voltage to VCC, I/O is high impedance Z. By all means, a read access to any address or an Answer-to-Reset must be carried out before data can be altered.

2.6 Break

If RST is set to high during CLK in state L any operation is aborted and I/O is switched to high impedance Z. Minimum duration of t_{RES} = 5 µs is necessary to trigger a defined valid reset. After Break the chip is ready for further operations.

2.7 Failures

Behavior in case of failures:

In case of one of the following failures, the chip sets the I/O to high impedance Z after 8 clock pulses at the latest.

Possible failures:

- Comparison unsuccessful
- Wrong command
- Wrong number of command clock pulses
- Write/erase access to already protected bytes
- Rewriting and erasing of a bit in the protection memory

2.8 Coding of the Chip

Due to security purposes every chip is irreversibly coded by a scheme. By this way fraud and misuse is excluded. The relevant data are programmed in the memory area from address 0 to 31. Afterwards the associated protection bits are programmed. As an example, **figures 12** and **13** show ATR and Directory Data of Structure 1. When delivered, ATR header, ICM and ICT are programmed. Siemens programs also the AID. The AID (Application IDentifier) consists of 5 byte RID (Registered application provider IDentifier) administered by a national registration authority and of up to 11 byte PIX (Proprietary application Identifier eXtension). There are two possibilities: the customers AID or Siemens AID (only for sample quantities). Depending on the agreement between the customer and Siemens ICCF can be also programmed before delivery.

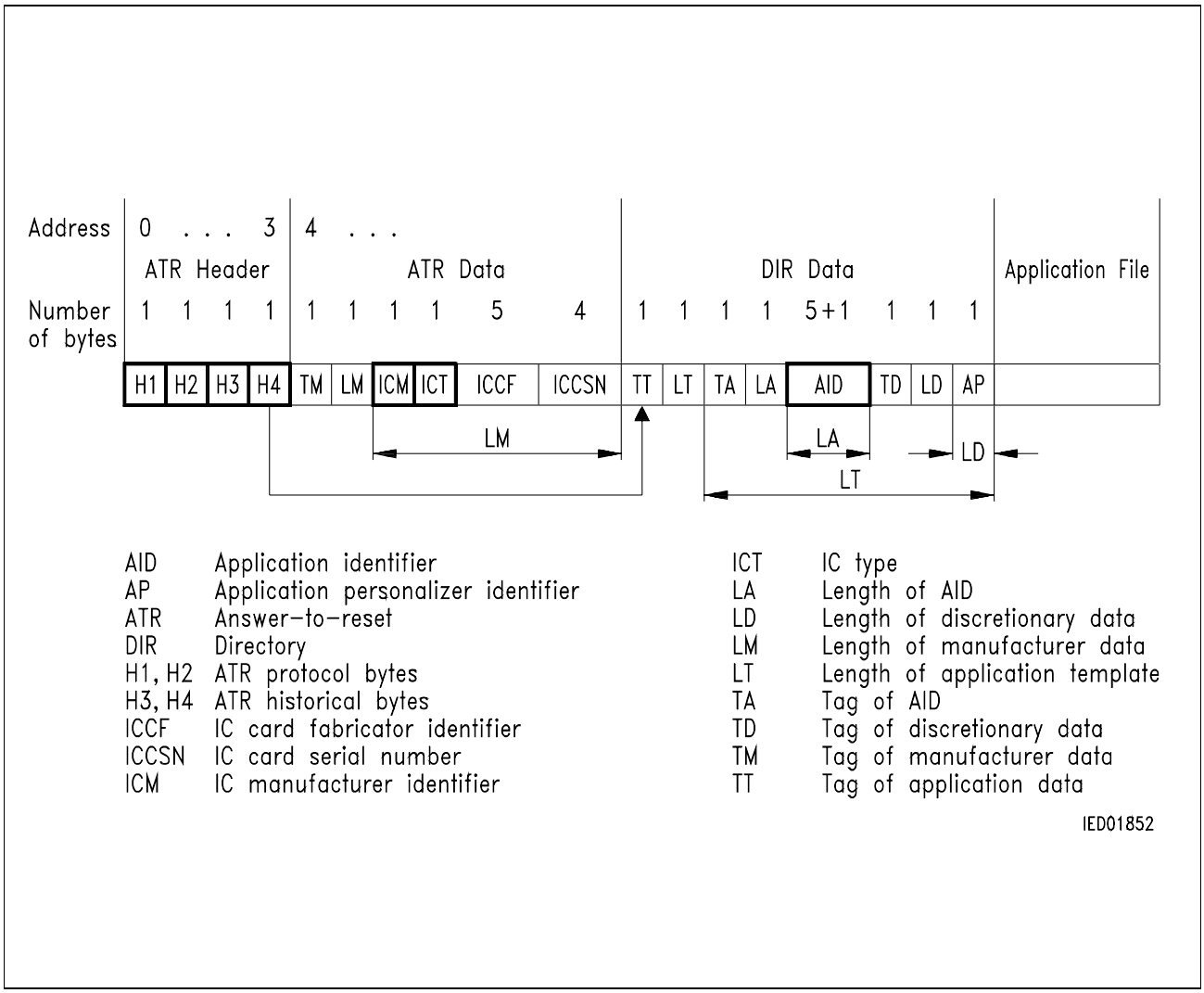


Figure 12
Synchronous Transmission
ATR and Directory Data of Structure 1

3 Operational Information

3.1 Memory Map

Address (decimal)	Main Memory	Protection Memory	Security Memory (only SLE 4442)
255	Data Byte 255 (D7 … D0)		
:	:		
32	Data Byte 32 (D7 … D0)		
31	Data Byte 31 (D7 … D0)	Protection Bit 31 (D31)	
:	:	:	
3	Data Byte 3 (D7 … D0)	Protection Bit 3 (D3)	Reference Data Byte 3 (D7 … D0)
2	Data Byte 2 (D7 … D0)	Protection Bit 2 (D2)	Reference Data Byte 2 (D7 … D0)
1	Data Byte 1 (D7 … D0)	Protection Bit 1 (D1)	Reference Data Byte 1 (D7 … D0)
0	Data Byte 0 (D7 … D0)	Protection Bit 0 (D0)	Error Counter (0,0,0,0,0,D2,D1,D0)

The Data bytes 0 to 31 can be protected against further changes by programming the associated protection bit 0 to 31. The SLE 4442 allows data changing only after correct verification of the Reference Data bytes. Reading of the Data bytes and of the associated protection bits is always possible.

3.2 Electrical Characteristics

3.2.1 Absolute Maximum Ratings

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Supply voltage	V_{CC}	– 0.3	6.0	V
Input voltage (any pin)	V_I	– 0.3	6.0	V
Storage temperature	T_{stg}	– 40	125	°C
Power dissipation	P_{tot}		70	mW

Note: Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this data sheet is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability, including EEPROM data retention and write/erase endurance.

In the operating range the functions given in the circuit description are fulfilled.

3.2.4 AC Characteristics

The AC characteristics refer to the timing diagrams in the following. V_{IHmin} and V_{ILmax} are reference levels for measuring timing of signals.

Parameter	Symbol	Limit Values			Unit	Test Condition
		min.	typ.	max.		
RST High to CLK Setup time	t_{10}	4			µs	
CLK Low to RST Hold time	t_{11}	4			µs	
RST High time (address reset)	t_{12}	20	50		µs	
RST Low to I/O Valid time	t_{13}			2.5	µs	
RST Low to CLK Setup time	t_{14}	4			µs	
CLK Frequency	f_{CLK}	7		50	kHz	
CLK Rise time	t_R			1	µs	
CLK Fall time	t_F			1	µs	
CLK High time	t_{15}	9			µs	
CLK Low time	t_{16}	9			µs	
CLK Low to I/O Valid time	t_{17}			2.5	µs	
Reset time for Break	t_{18}	5			µs	
RST High to I/O Clear time (Break)	t_{19}	2.5			µs	
I/O High time (Start Condition)	t_1	10			µs	
CLK High to I/O Hold time	t_2	4			µs	
I/O Low to CLK Hold time (Start Condition)	t_3	4			µs	
I/O Setup to CLK High time	t_4	1			µs	
CLK Low to I/O Hold time	t_5	1			µs	
CLK High to I/O Clear time (Stop Condition)	t_6	4			µs	
CLK Low to I/O Valid time	t_7			2.5	µs	
CLK Low to I/O Valid time	t_8			2.5	µs	
CLK Low to I/O Clear time	t_9			2.5	µs	
Erase time	t_{ER}	2.5			ms	f_{CLK} = 50 kHz
Write time	t_{WR}	2.5			ms	f_{CLK} = 50 kHz
Power on reset time	t_{POR}			100	µs	

Note: The listed characteristics are ensured over the operating range of the integrated circuit. Typical characteristics specify mean values expected over the production spread. If not otherwise specified, typical characteristics apply at T_A = 25 °C and the given supply voltage.

3.3 Timing Diagrams

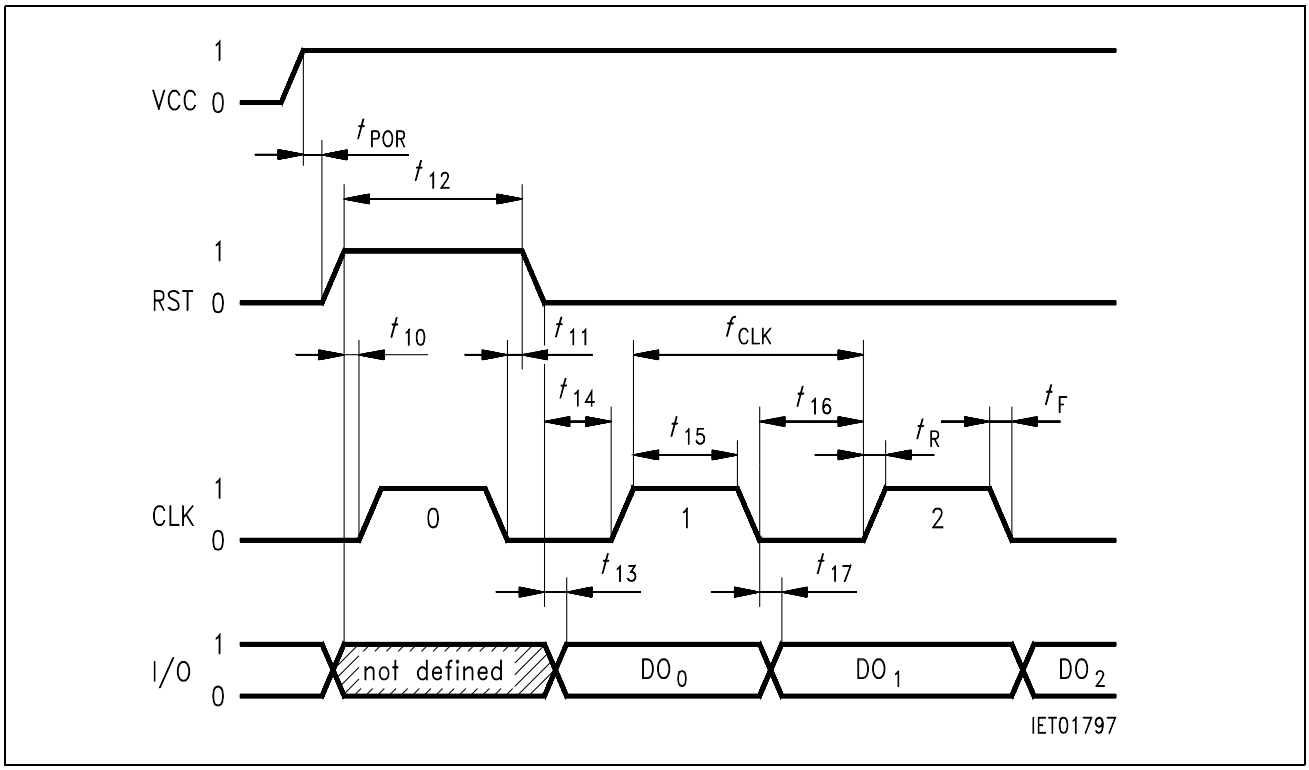


Figure 14
Reset and Answer-to-Reset

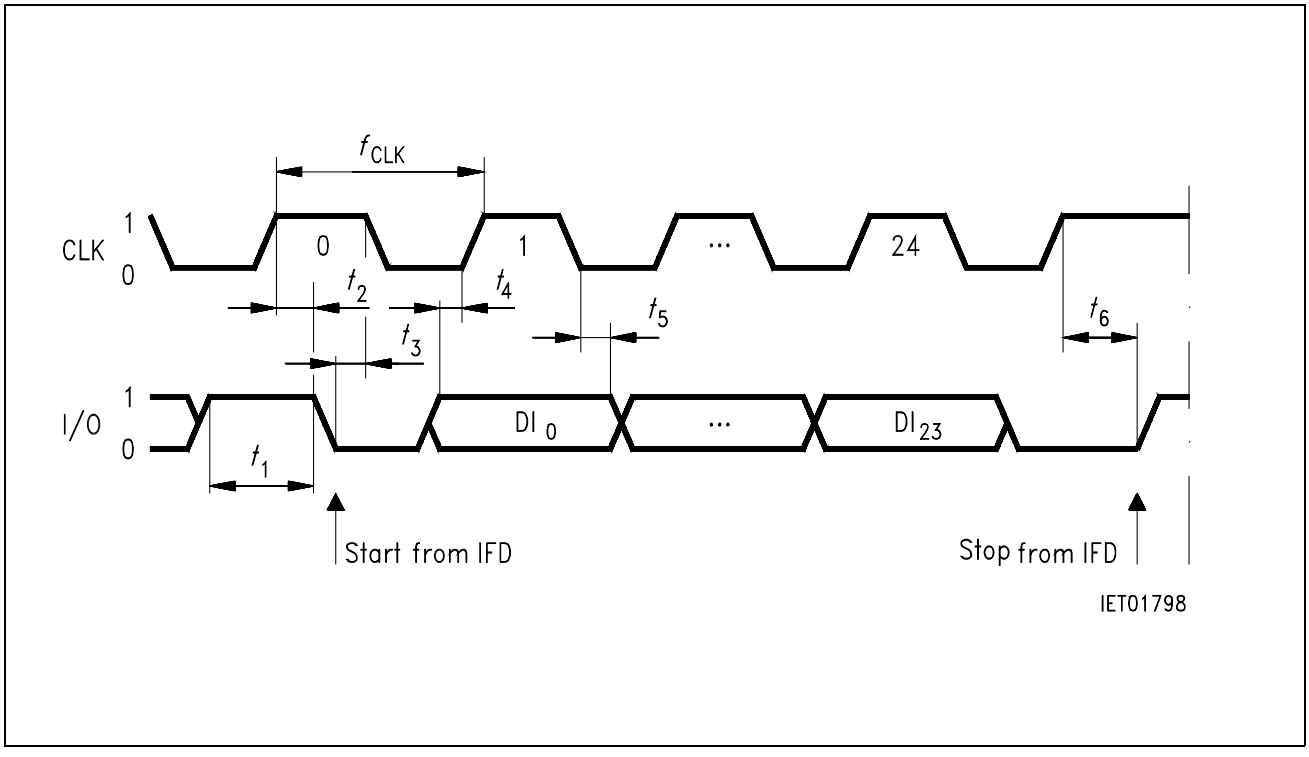


Figure 15
Command Mode

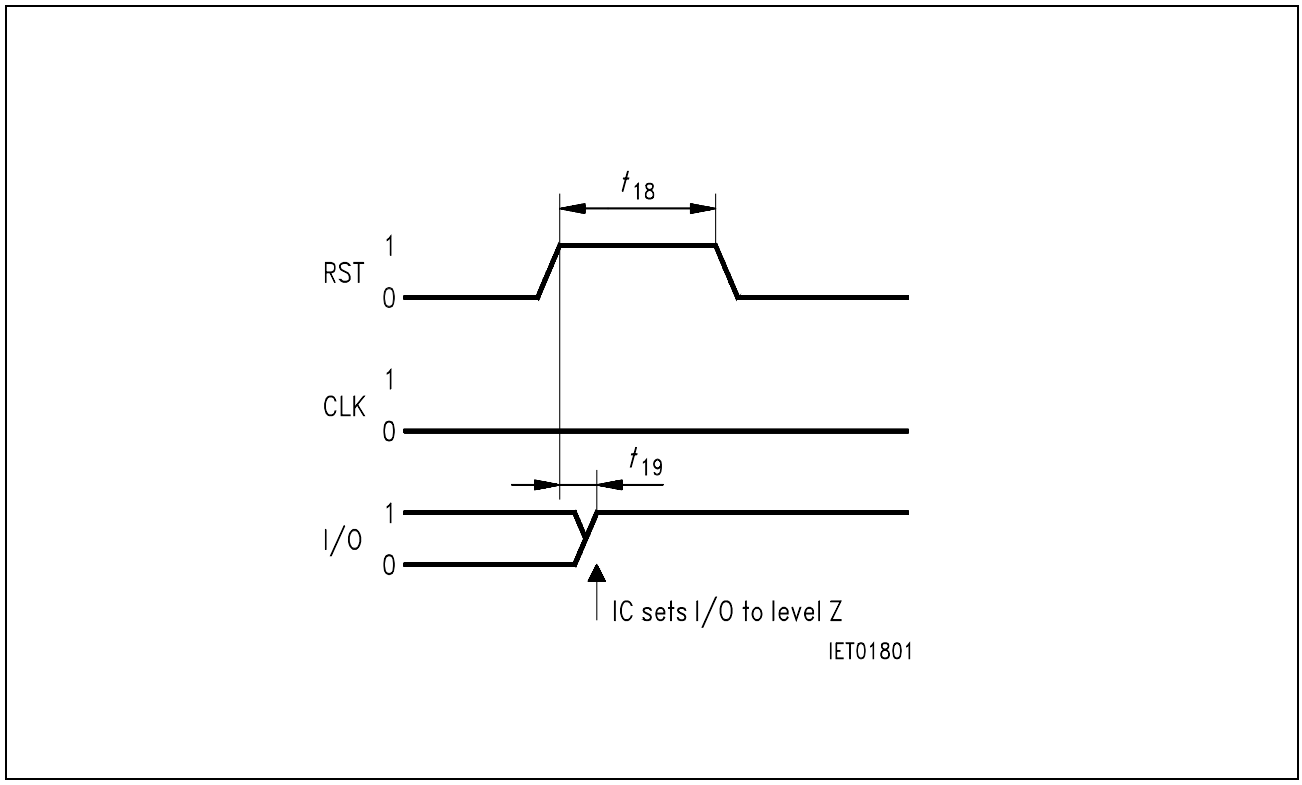
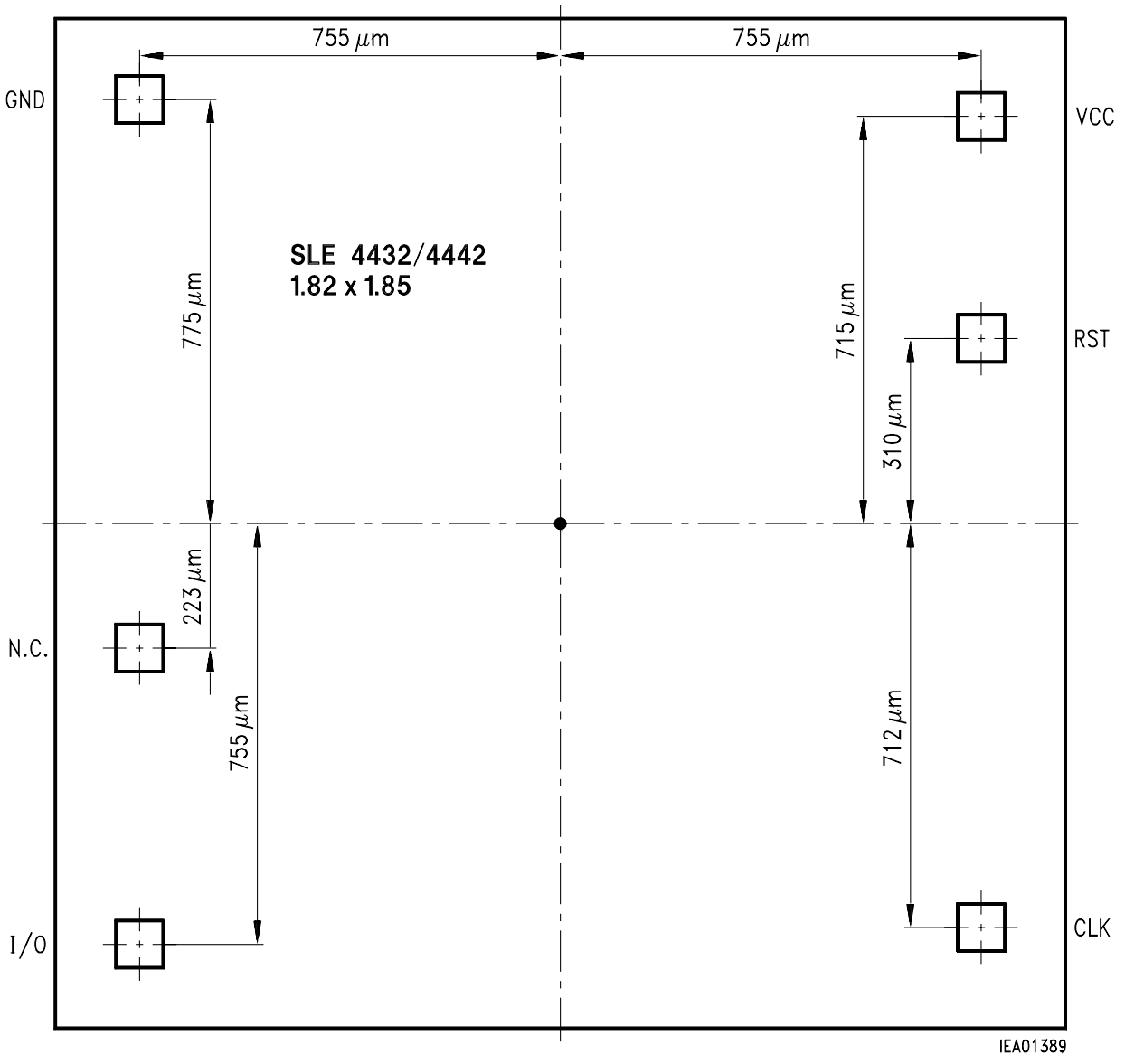


Figure 18
Break

Wafer Size: 5"
Stepping Size: 1820 × 1850 µm²

Scribe Line: 80 µm
Pad Size: 110 × 110 µm²



Chip Dimensions